

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ C7

600V CoolMOS™ C7 Power Transistor
IPA60R060C7

Data Sheet

Rev. 2.0
Final

1 Description

CoolMOS™ C7 is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies.

600V CoolMOS™ C7 series combines the experience of the leading SJ MOSFET supplier with high class innovation.

The 600V C7 is the first technology ever with $R_{DS(on)} \cdot A$ below $10\text{m}\Omega \cdot \text{mm}^2$.

Features

- Suitable for hard and soft switching (PFC and high performance LLC)
- Increased MOSFET dv/dt ruggedness to 120V/ns
- Increased efficiency due to best in class FOM $R_{DS(on)} \cdot E_{oss}$ and $R_{DS(on)} \cdot Q_g$
- Best in class $R_{DS(on)}$ /package
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Benefits

- Increased economies of scale by use in PFC and PWM topologies in the application
- Higher dv/dt limit enables faster switching leading to higher efficiency
- Enabling higher system efficiency by lower switching losses
- Increased power density solutions due to smaller packages
- Suitable for applications such as server, telecom and solar
- Higher switching frequencies possible without loss in efficiency due to low E_{oss} and Q_g

Applications

PFC stages and PWM stages (TTF, LLC) for high power/performance SMPS e.g. Computing, Server, Telecom, UPS and Solar.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

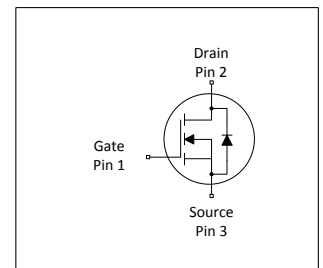


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	60	$\text{m}\Omega$
$Q_{g,typ}$	68	nC
$I_{D,pulse}$	135	A
$I_{D,continuous} @ T_j < 150^\circ\text{C}$	54	A
$E_{oss}@400\text{V}$	8.1	μJ
Body diode di/dt	420	$\text{A}/\mu\text{s}$

Type / Ordering Code	Package	Marking	Related Links
IPA60R060C7	PG-TO 220 FullPAK	60C7060	see Appendix A

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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	16 10	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	135	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	159	mJ	$I_D=6.4\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	0.80	mJ	$I_D=6.4\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, single pulse	I_{AS}	-	-	6.4	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	120	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	34	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	50	Ncm	M2.5 screws
Continuous diode forward current	I_S	-	-	16	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	135	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	20	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq 9.9\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di/dt	-	-	420	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq 9.9\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage	V_{ISO}	-	-	2500	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$.

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch

3 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	3.69	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	80	°C/W	lead
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	-	-	°C/W	n.a.
Soldering temperature, wavesoldering only allowed at leads	T_{sld}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

4 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0V$, $I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}$, $I_D=0.8mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=600$, $V_{GS}=0V$, $T_j=25^\circ\text{C}$ $V_{DS}=600$, $V_{GS}=0V$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V$, $V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.052 0.115	0.060 -	Ω	$V_{GS}=10V$, $I_D=15.9A$, $T_j=25^\circ\text{C}$ $V_{GS}=10V$, $I_D=15.9A$, $T_j=150^\circ\text{C}$
Gate resistance	R_G	-	0.8	-	Ω	$f=1MHz$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	2850	-	pF	$V_{GS}=0V$, $V_{DS}=400V$, $f=250kHz$
Output capacitance	C_{oss}	-	54	-	pF	$V_{GS}=0V$, $V_{DS}=400V$, $f=250kHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	101	-	pF	$V_{GS}=0V$, $V_{DS}=0...400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	1050	-	pF	$I_D=\text{constant}$, $V_{GS}=0V$, $V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	15.5	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=15.9A$, $R_G=3.3\Omega$; see table 9
Rise time	t_r	-	11	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=15.9A$, $R_G=3.3\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	79	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=15.9A$, $R_G=3.3\Omega$; see table 9
Fall time	t_f	-	4	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=15.9A$, $R_G=3.3\Omega$; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	14	-	nC	$V_{DD}=400V$, $I_D=15.9A$, $V_{GS}=0$ to $10V$
Gate to drain charge	Q_{gd}	-	23	-	nC	$V_{DD}=400V$, $I_D=15.9A$, $V_{GS}=0$ to $10V$
Gate charge total	Q_g	-	68	-	nC	$V_{DD}=400V$, $I_D=15.9A$, $V_{GS}=0$ to $10V$
Gate plateau voltage	$V_{plateau}$	-	5.0	-	V	$V_{DD}=400V$, $I_D=15.9A$, $V_{GS}=0$ to $10V$

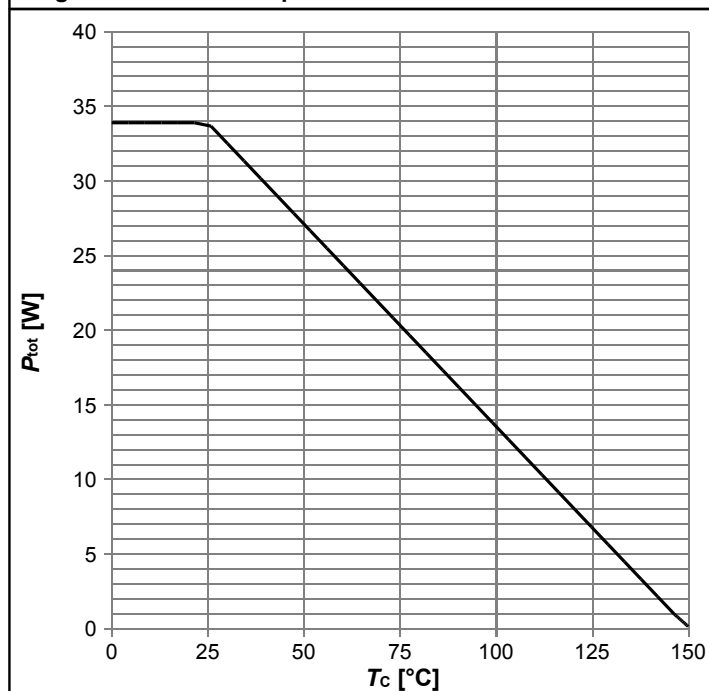
¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

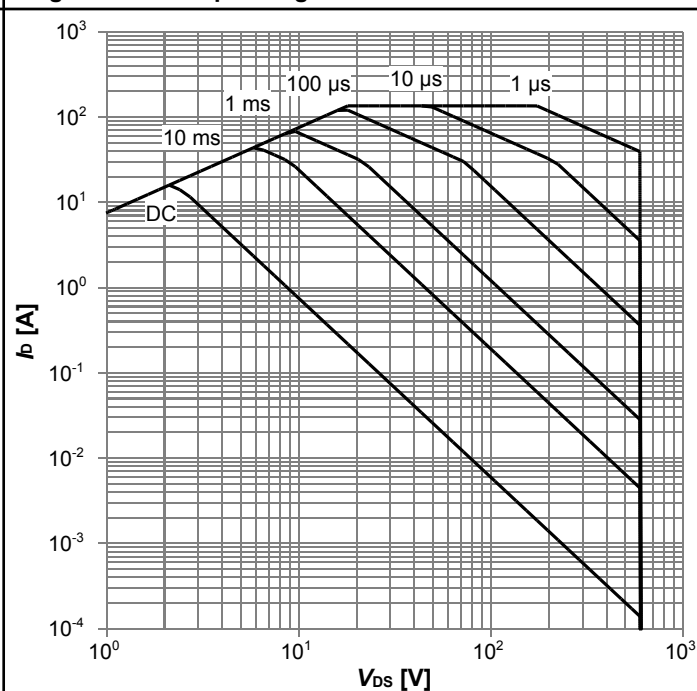
Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=15.9A$, $T_J=25^{\circ}C$
Reverse recovery time	t_{rr}	-	390	-	ns	$V_R=400V$, $I_F=15.9A$, $di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	6	-	μC	$V_R=400V$, $I_F=15.9A$, $di_F/dt=100A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	32	-	A	$V_R=400V$, $I_F=15.9A$, $di_F/dt=100A/\mu s$; see table 8

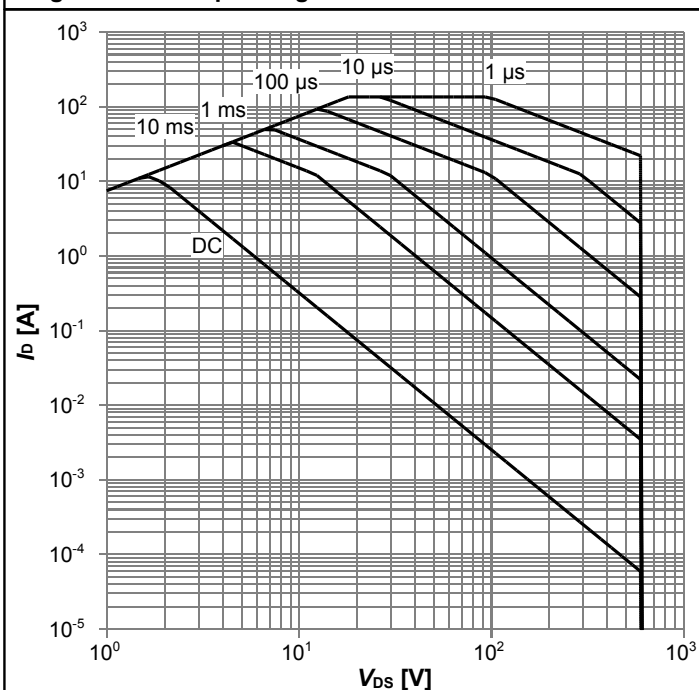
5 Electrical characteristics diagrams

Diagram 1: Power dissipation


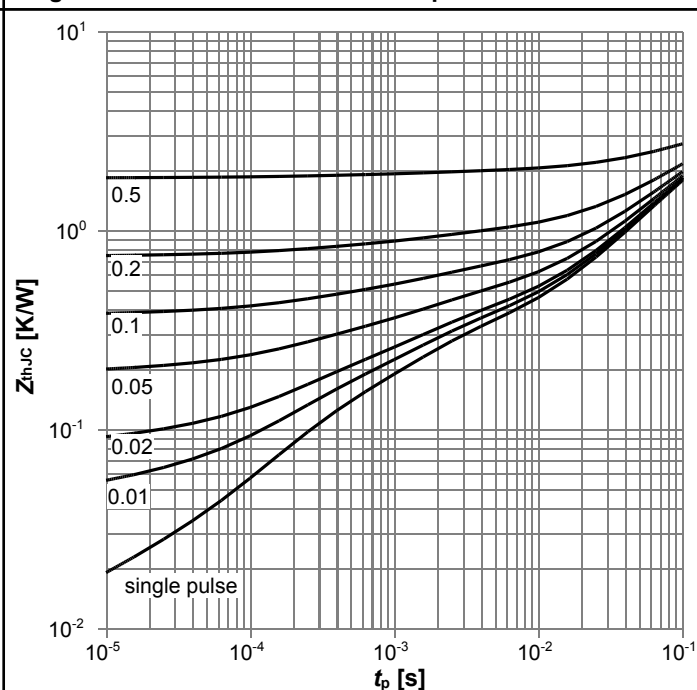
$$P_{tot}=f(T_c)$$

Diagram 2: Safe operating area


$$I_D=f(V_{DS}); T_c=25\text{ °C}; D=0; \text{parameter: } t_p$$

Diagram 3: Safe operating area


$$I_D=f(V_{DS}); T_c=80\text{ °C}; D=0; \text{parameter: } t_p$$

Diagram 4: Max. transient thermal impedance


$$Z_{thJC}=f(t_p); \text{parameter: } D=t_p/T$$

Diagram 5: Typ. output characteristics

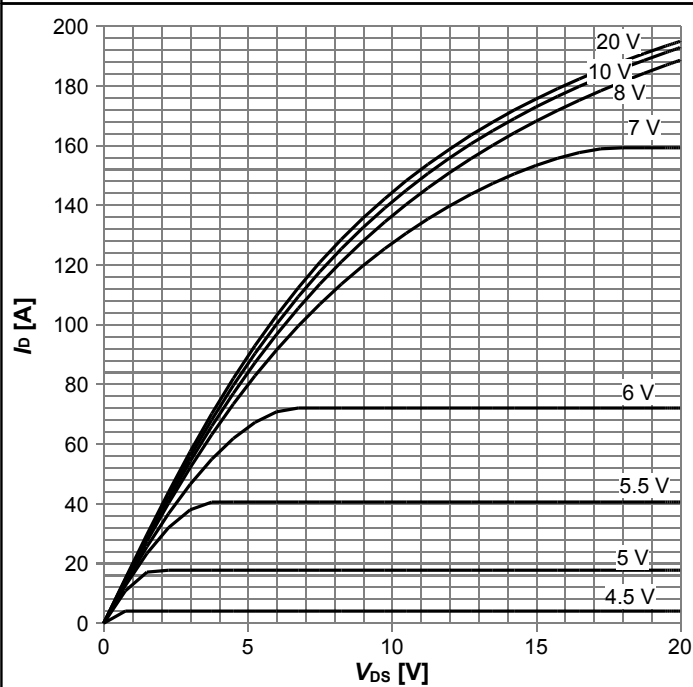

 $I_D = f(V_{DS}); T_J = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. output characteristics

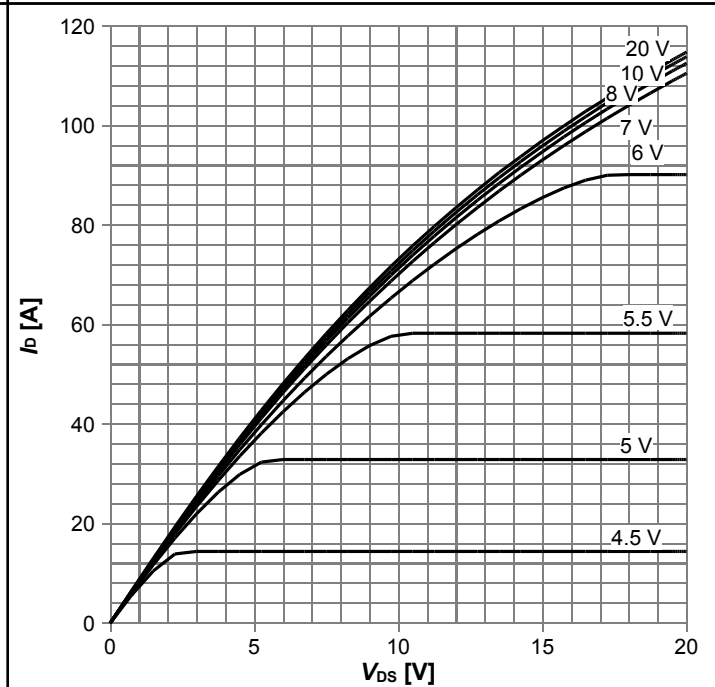

 $I_D = f(V_{DS}); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. drain-source on-state resistance

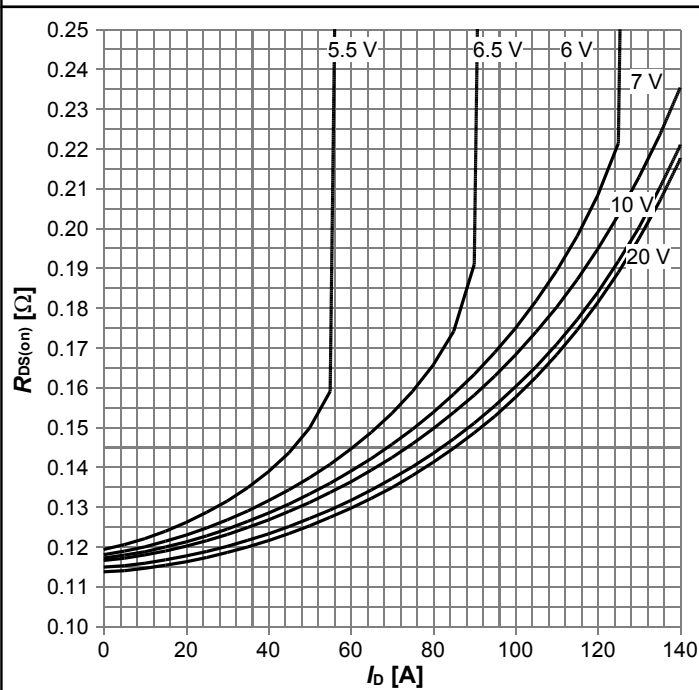

 $R_{DS(on)} = f(I_D); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 8: Drain-source on-state resistance

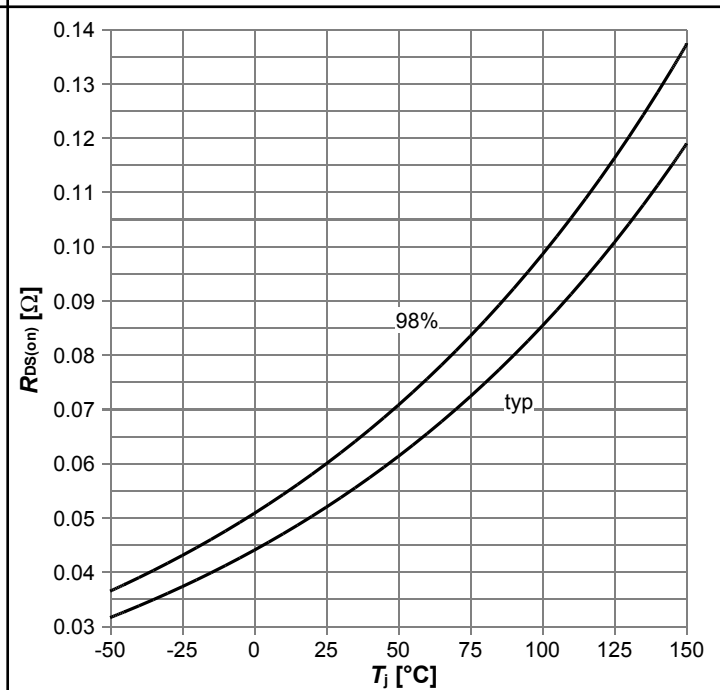

 $R_{DS(on)} = f(T_J); I_D = 15.9\text{ A}; V_{GS} = 10\text{ V}$

Diagram 9: Typ. transfer characteristics

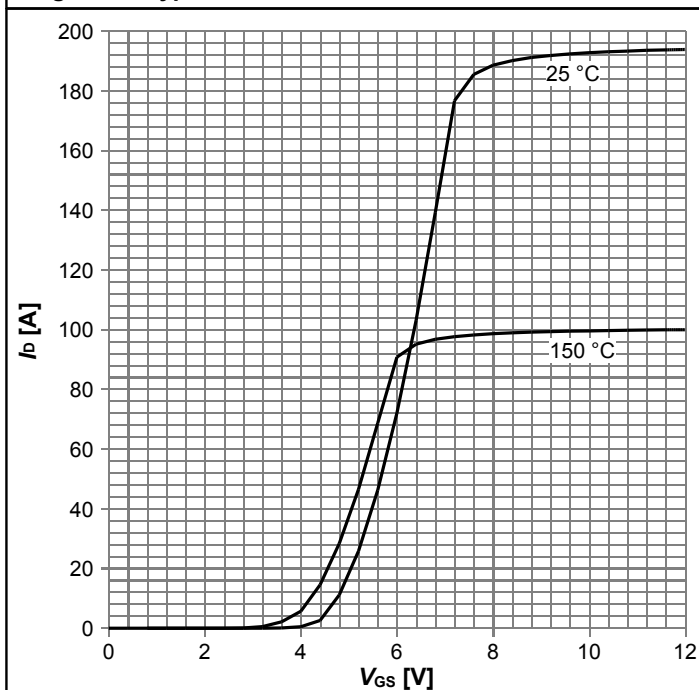

 $I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge

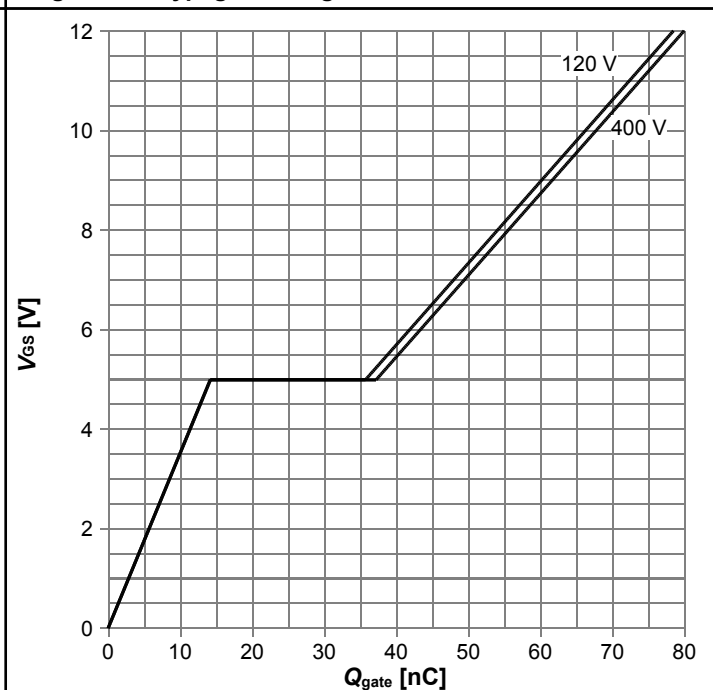

 $V_{GS} = f(Q_{gate}); I_D = 15.9 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode

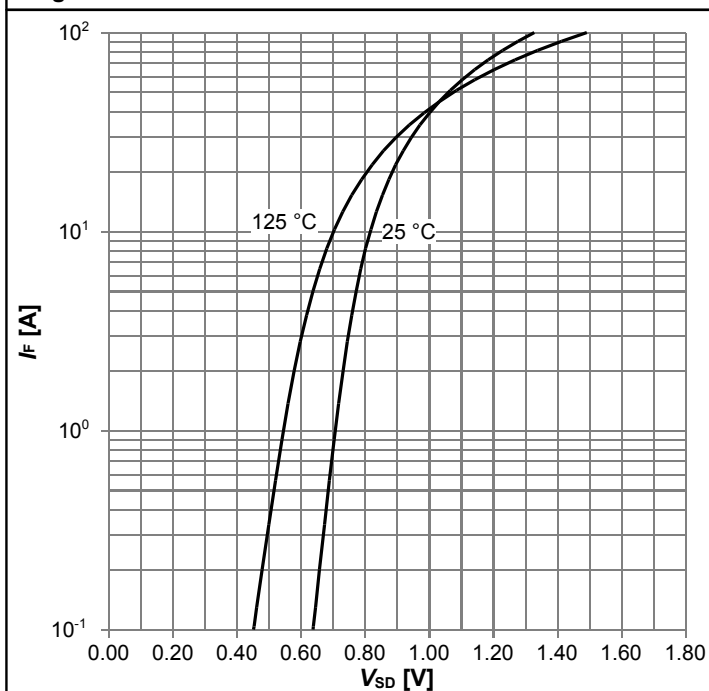

 $I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 12: Avalanche energy

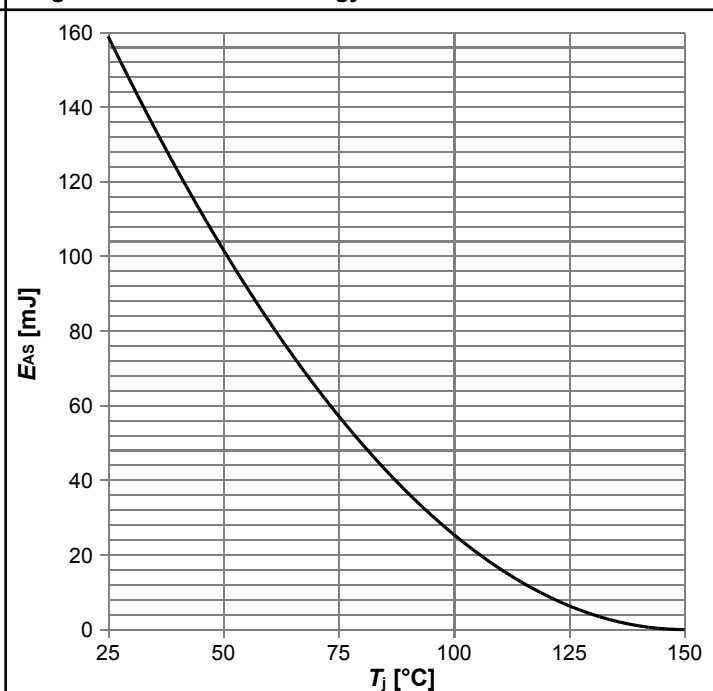
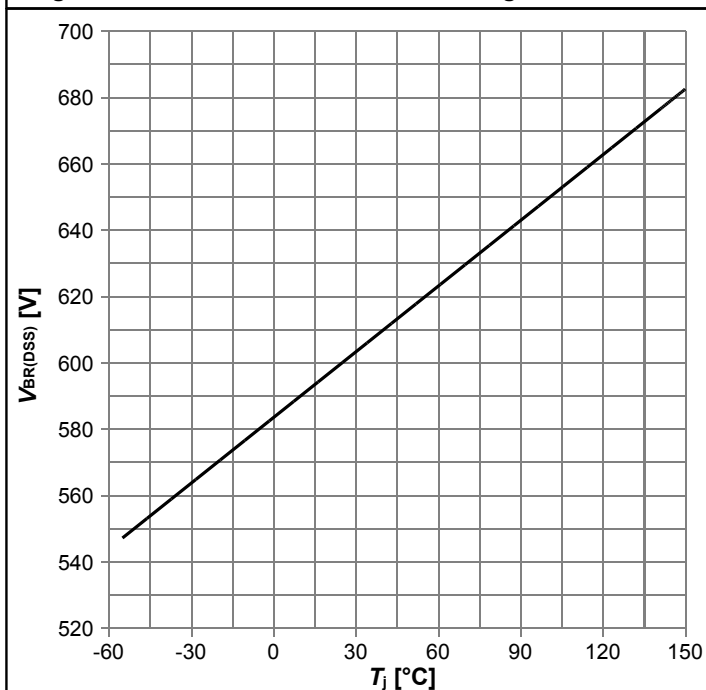
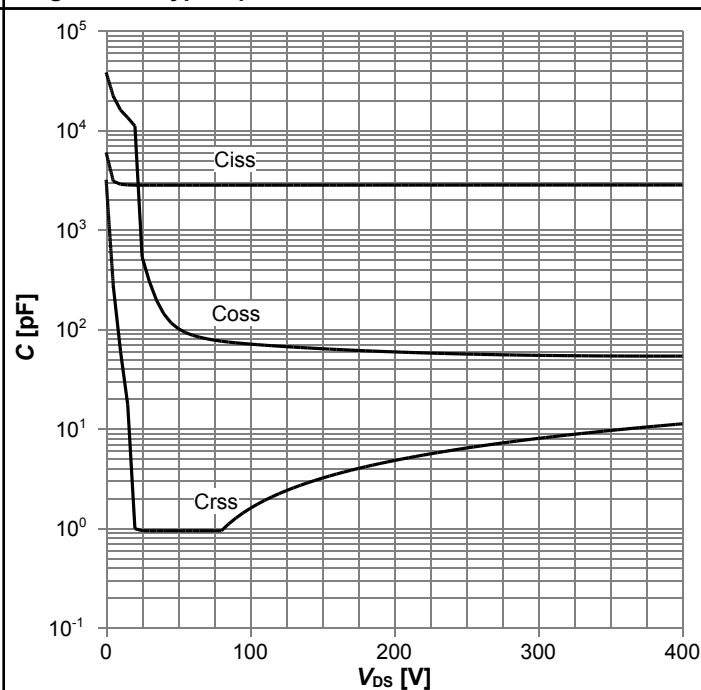

 $E_{AS} = f(T_j); I_D = 6.4 \text{ A}; V_{DD} = 50 \text{ V}$

Diagram 13: Drain-source breakdown voltage



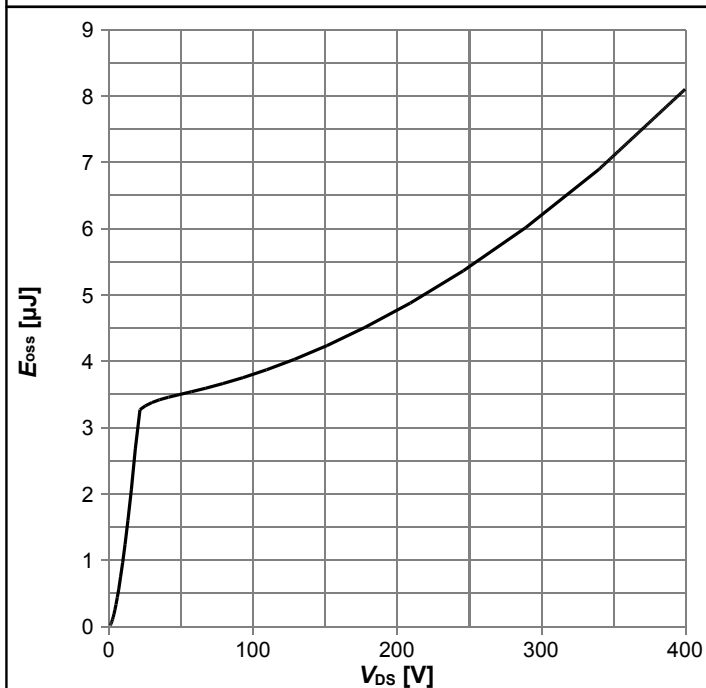
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 14: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$$

Diagram 15: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

6 Test Circuits

Table 8 Diode characteristics

Figure 1 consists of two parts. The left part is a schematic diagram of a test circuit for diode characteristics. It shows two diodes connected in series, each with a gate resistor R_{g1} and R_{g2} . The diodes are connected to a common load inductor. The forward current I_F is measured through the inductor. The reverse voltage V_{DS} is measured across the diodes. The gate resistors are equal, $R_{g1} = R_{g2}$. The right part is a graph of the diode recovery waveform. The vertical axis represents voltage V and current I . The horizontal axis represents time t . The forward current I_F is shown as a solid line, and the reverse current I_{rm} is shown as a dashed line. The forward voltage V_{DS} is shown as a solid line, and the reverse voltage $V_{DS(peak)}$ is shown as a dashed line. The forward recovery time t_F is the time from the start of the reverse current to the point where the reverse current is 10% of the forward current. The reverse recovery time t_{rr} is the time from the start of the reverse current to the point where the reverse current is 10% of the forward current. The storage time t_s is the time from the point where the reverse current is 10% of the forward current to the end of the reverse current. The forward charge Q_F is the area under the forward current curve, and the reverse charge Q_s is the area under the reverse current curve. The total reverse charge Q_{rr} is the sum of Q_F and Q_s .

Table 9 Switching times

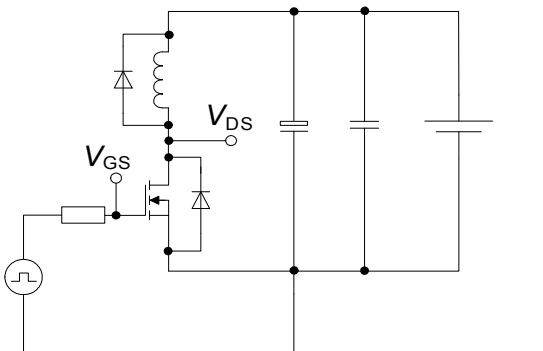
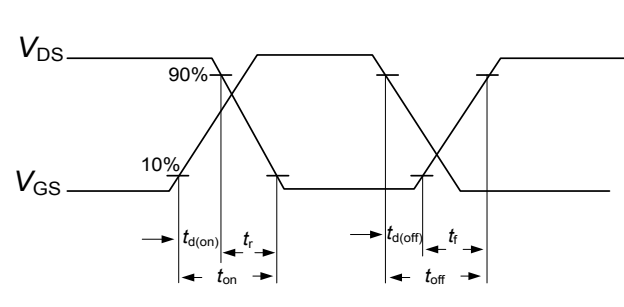
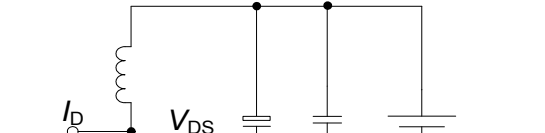
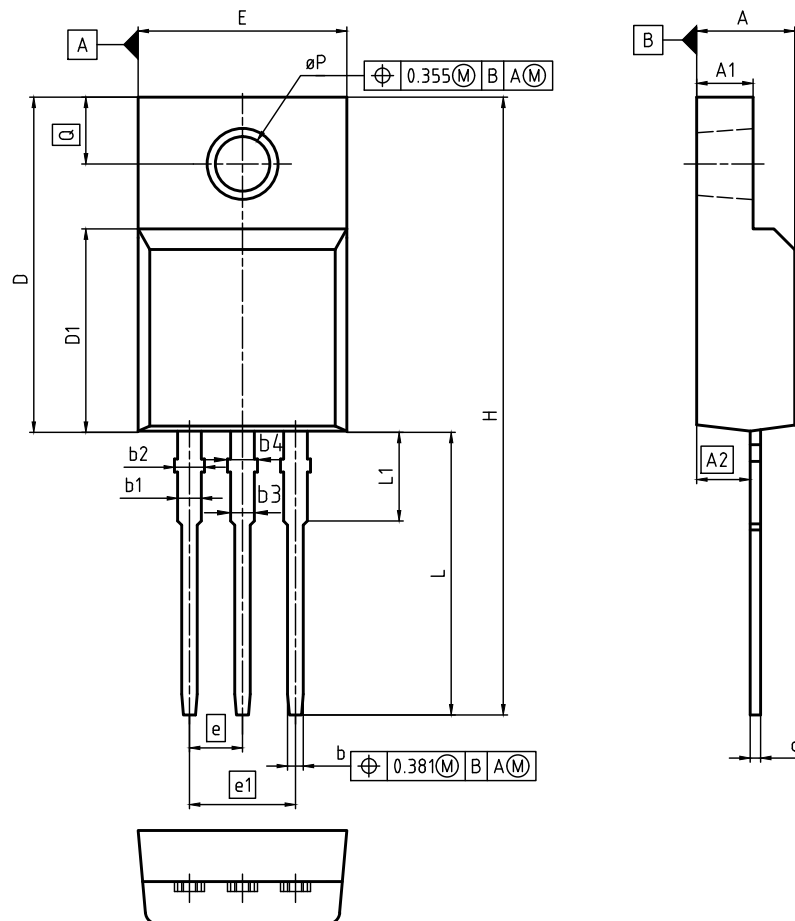
Switching times test circuit for inductive load	Switching times waveform
 The circuit diagram illustrates a switching test setup for an inductive load. A MOSFET is driven by a pulse source through a gate resistor. The drain is connected to an inductor and a freewheeling diode. A load capacitor is connected in parallel with the inductor. The drain-source voltage V_{DS} is measured across the MOSFET.	 The timing diagram shows the relationship between the drain-source voltage V_{DS} and the gate-source voltage V_{GS} during switching transitions. Key time intervals are defined: $t_{d(on)}$: Delay time from 10% V_{GS} to 90% V_{DS}. t_r: Rise time from 90% V_{DS} to 100% V_{DS}. t_f: Fall time from 90% V_{DS} to 10% V_{DS}. $t_{d(off)}$: Delay time from 10% V_{GS} to 90% V_{DS}. t_{off}: Total turn-off time from 10% V_{GS} to 10% V_{DS}.

Table 10 **Unclamped inductive load**

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package Outlines



DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.50	4.90	0.177	0.193
A1	2.34	2.85	0.092	0.112
A2	2.42	2.86	0.095	0.113
b	0.65	0.90	0.026	0.035
b1	0.95	1.38	0.037	0.054
b2	0.95	1.51	0.037	0.059
b3	0.65	1.38	0.026	0.054
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.67	16.15	0.617	0.636
D1	8.97	9.83	0.353	0.387
E	10.00	10.65	0.394	0.419
e	2.54 (BSC)		0.100 (BSC)	
e1	5.08		0.200	
N	3		3	
H	28.70	29.75	1.130	1.171
L	12.78	13.75	0.503	0.541
L1	2.83	3.45	0.111	0.136
øP	2.95	3.38	0.116	0.133
Q	3.15	3.50	0.124	0.138

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EUROPEAN PROJECTION 	
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REVISION 05	

Figure 1 Outline PG-TO 220 FullPAK, dimensions in mm/inches

8 Appendix A

Table 11 Related Links

- IFX CoolMOS™ C7 Webpage: www.infineon.com
- IFX CoolMOS™ C7 application note: www.infineon.com
- IFX CoolMOS™ C7 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPA60R060C7

Revision: 2015-12-01, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2015-12-01	Release of final version

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

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The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.



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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
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- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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